TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

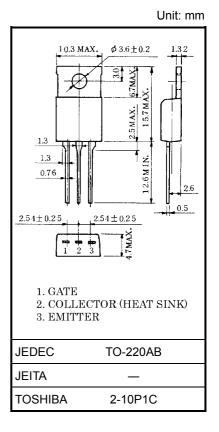
GT40G121

The 4th Generation Current Resonance Inverter Switching Applications

- Enhancement-mode
- High speed: $t_f = 0.30 \mu s$ (typ.) (IC = 60 A)
- Low saturation voltage: VCE (sat) = 1.8 V (typ.) (IC = 60 A)

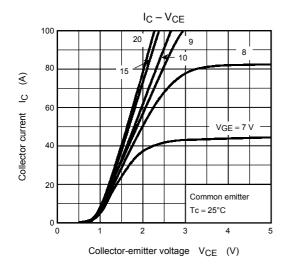
Maximum Ratings (Ta = 25°C)

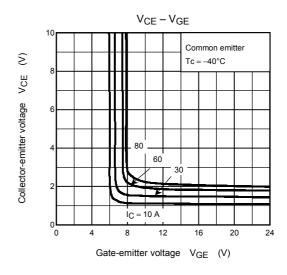
Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	400	V	
Gate-emitter voltage		V_{GES}	±25	V	
Collector current	DC	IC	40	Α	
	1 ms	I _{CP}	100		
Collector power dissipation (Tc = 25°C)		PC	100	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

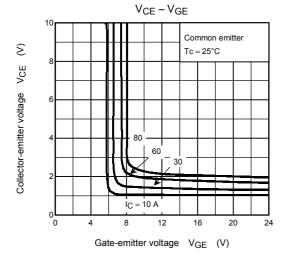


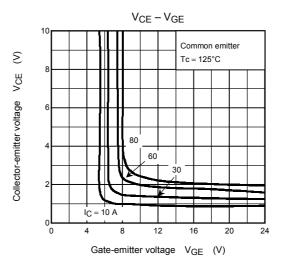
Electrical Characteristics (Ta = 25°C)

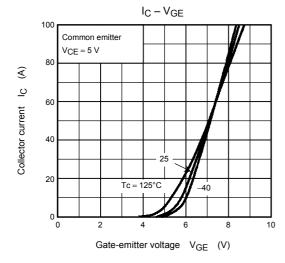
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0$	_	_	±500	nA
Collector cut-off current		I _{CES}	V _{CE} = 400 V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE} (OFF)	$I_C = 60 \text{ mA}, V_{CE} = 5 \text{ V}$	3.0	_	6.0	٧
Collector-emitter saturation voltage		V _{CE (sat)}	$I_C = 60 \text{ A}, V_{GE} = 15 \text{ V}$	_	1.8	2.5	>
Input capacitance		C _{ies}	$V_{CE} = 10 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$	_	3900		pF
Switching time	Rise time	t _r	39 Ω CI EEE EE E	_	0.33		- μs
	Turn-on time	t _{on}		_	0.43	_	
	Fall time	t _f		_	0.30	0.40	
	Turn-off time	t _{off}		_	0.54	_	
Thermal resistance		R _{th(j-c)}	_	_	_	1.25	°C/W

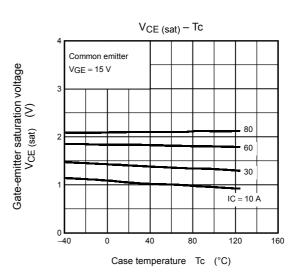




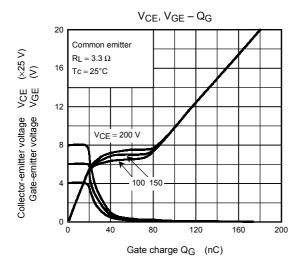


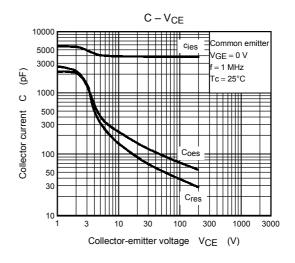


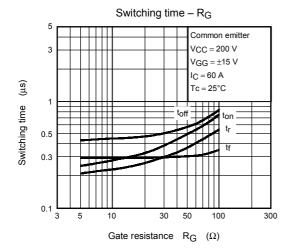


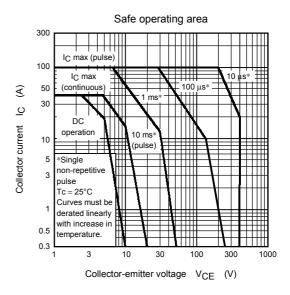


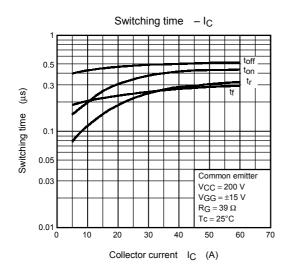
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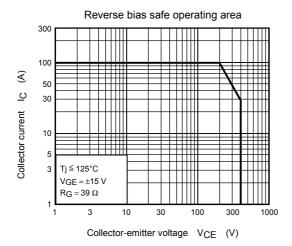


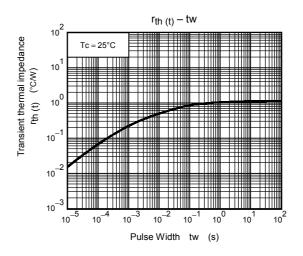






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